Q. Metrology, Inspection, and Yield Enhancement 분과

2017년 2월 15일 (수), 15:25-17:10
Room C (사파이어, 2층)

[WC4-Q] Metrology and Inspection (II)

좌장: 김진승(전북대학교), 조용재(한국반도체연구조합)

WC4-Q-1 **15:25-15:55**	**[초청]** **A Multi-Beam Scanning Electron Microscope for High Resolution and High Throughput** Byung Joon Park *Microscopy Division, Carl Zeiss Korea*
WC4-Q-2 **15:55-16:10**	**In-Line Scatterometry for Dynamic Nano-Pattern Uniformity Evaluation** Daesuk Kim[1], Vamara Dembele[1], Inho Choi[1], Ramachandran Kasu[1], HyungJoon Lim[2], GeeHong Kim[2], and Jaejong Lee[2] *[1]Division of Mechanical System Engineering, Chonbuk National University, [2]Nano-Mechanical Systems Research Center, Korea Institute of Machinery and Materials*
WC4-Q-3 **13:25-13:40**	**Close Loop to Fix the Systematic Failure Using Volume Diagnostics** Jeongsu Park[1], Kiheung Park[2], and Joohyun Park[2] *[1]Synopsys, Inc., SEG, Yield and Failure Analysis, [2]Design Service Team, System LSI, Samsung Electronics Co., Ltd.*
WC4-Q-4 **16:25-16:55**	**[초청]** **Room Temperature Photoluminescence (RTPL) Characterization of Silicon Wafers towards In-Line Inspection and Monitoring** Woo Sik Yoo *WaferMasters, Inc.*
WC4-Q-5 **16:55-17:10**	**Strain Mapping in a Nanoscale-Triangular SiGe Pattern by Dark-Field Electron Holography with Medium Magnification Mode** Van Vuong Hoang[1,2], Jung Ho Yoo[1], Soon-Ku Hong[3], and Jun-Mo Yang[1] *[1]Department of Measurement & Analysis, National Nanofab Center, [2]Department of Materials Science and Engineering, Chungnam National University*